

Georges Pavlidis

List of Publications by Year in descending order

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815
citing authors

#	ARTICLE	IF	CITATIONS
1	Micro to Nano: Multiscale IR Analyses Reveal Zinc Soap Heterogeneity in a 19th-Century Painting by Corot. <i>Analytical Chemistry</i> , 2022, 94, 3103-3110.	6.5	18
2	High Throughput Nanoimaging of Thermal Conductivity and Interfacial Thermal Conductance. <i>Nano Letters</i> , 2022, 22, 4325-4332.	9.1	12
3	Gate resistance thermometry: An electrical thermal characterization technique. , 2022, , 201-221.		0
4	Nanoscale IR spectroscopy: From Principles to Nanoscale Imaging and Identification of Metal Soaps. <i>Microscopy and Microanalysis</i> , 2021, 27, 2814-2815.	0.4	0
5	Experimental confirmation of long hyperbolic polariton lifetimes in monoisotopic (10B) hexagonal boron nitride at room temperature. <i>APL Materials</i> , 2021, 9, .	5.1	16
6	Monitoring the Joule heating profile of GaN/SiC high electron mobility transistors via cross-sectional thermal imaging. <i>Journal of Applied Physics</i> , 2020, 128, 075705.	2.5	10
7	Thermal Performance of GaN/Si HEMTs Using Near-Bandgap Thermoreflectance Imaging. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 822-827.	3.0	23
8	Revealing the Distribution of Metal Carboxylates in Oil Paint from the Micro to Nanoscale. <i>Angewandte Chemie</i> , 2019, 131, 11778-11782.	2.0	7
9	Revealing the Distribution of Metal Carboxylates in Oil Paint from the Micro to Nanoscale. <i>Angewandte Chemie - International Edition</i> , 2019, 58, 11652-11656.	13.8	28
10	The Effects of AlN and Copper Back Side Deposition on the Performance of Etched Back GaN/Si HEMTs. <i>IEEE Electron Device Letters</i> , 2019, 40, 1060-1063.	3.9	20
11	Scalable Modeling of Transient Self-Heating of GaN High-Electron-Mobility Transistors Based on Experimental Measurements. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 2139-2145.	3.0	8
12	Spontaneous current constriction in threshold switching devices. <i>Nature Communications</i> , 2019, 10, 1628.	12.8	51
13	The Impact of Temperature on GaN/Si HEMTs Under RF Operation Using Gate Resistance Thermometry. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 330-336.	3.0	5
14	Thermal characterization of gallium nitride p-i-n diodes. <i>Applied Physics Letters</i> , 2018, 112, .	3.3	42
15	A Comparative Study on the Junction Temperature Measurements of LEDs With Raman Spectroscopy, Microinfrared (IR) Imaging, and Forward Voltage Methods. <i>IEEE Transactions on Components, Packaging and Manufacturing Technology</i> , 2018, 8, 1914-1922.	2.5	16
16	Transient Thermal Characterization of AlGaIn/GaN HEMTs Under Pulsed Biasing. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 1753-1758.	3.0	37
17	Improving the Transient Thermal Characterization of GaN HEMTs. , 2018, , .		8
18	Electrical and Thermal Analysis of Vertical GaN-on-GaN PN Diodes. , 2018, , .		3

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19	Characterization of AlGaIn/GaN HEMTs Using Gate Resistance Thermometry. IEEE Transactions on Electron Devices, 2017, 64, 78-83.	3.0	39
20	Steady State and Transient Thermal Characterization of Vertical GaN PIN Diodes. , 2017, , .		2
21	Thermal characterization of GaN vertical p-i-n diodes. , 2017, , .		2
22	The thermal effects of substrate removal on GaN HEMTs using Raman Thermometry. , 2016, , .		9
23	Thermal raman and IR measurement of heterogeneous integration stacks. , 2016, , .		3
24	Field-effect transistors based on wafer-scale, highly uniform few-layer p-type WSe ₂ . Nanoscale, 2016, 8, 2268-2276.	5.6	58
25	Thermal simulation of heterogeneous GaN/ InP/silicon 3DIC stacks. , 2015, , .		5
26	High Resolution Thermal Characterization and Simulation of Power AlGaIn/GaN HEMTs Using Micro-Raman Thermography and 800 Picosecond Transient Thermoreflectance Imaging. , 2014, , .		29